

Features

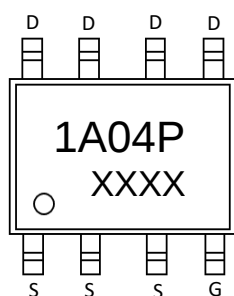
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-100V	320mΩ@-10V	-4A
	350mΩ@-4.5V	

Application

- Battery and loading switching
- Excellent package for good heat dissipation

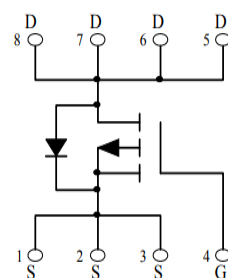


1A04P: Device code
 XXXX : Code

Marking and pin assignment



SOP-8 top view



Schematic diagram



Pb-Free



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)			
V_{DS}	Drain-Source Breakdown Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$ -4	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$ -20	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$ -4	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$ 2.5	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	75	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MQ1A04P	SOP-8	1A04P	3,000	6,000	42,000	13"reel

Electrical Characteristics (TJ=25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-100	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-100V, V _{GS} =0V	--	--	-1.0	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.0	--	-2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-4A	--	320	420	mΩ
		V _{GS} =-4.5V, I _D =-2A	--	350	500	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, f=1MHz	--	970	--	pF
C _{OSS}	Output Capacitance		--	26	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	21	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-50V, I _D =-4A, V _{GS} =-10V	--	19	--	nC
Q _{gs}	Gate Source Charge		--	4.6	--	nC
Q _{gd}	Gate Drain Charge		--	1.8	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-50V, I _D =-4A, V _{GS} =-10V, R _G =3.9Ω	--	5.8	--	nS
t _r	Turn-on Rise Time		--	2.8	--	nS
t _{d(off)}	Turn-Off Delay Time		--	28	--	nS
t _f	Turn-Off Fall Time		--	18	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	Tj=25°C, Is=-4A	--	-0.8	-1.2	V

Typical Operating Characteristics

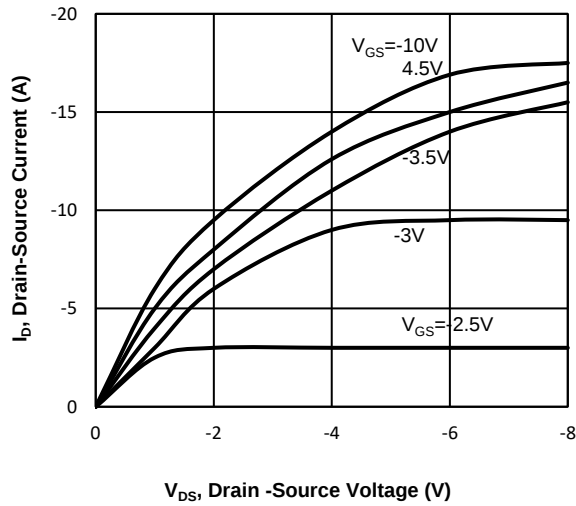


Fig1. Typical Output Characteristics

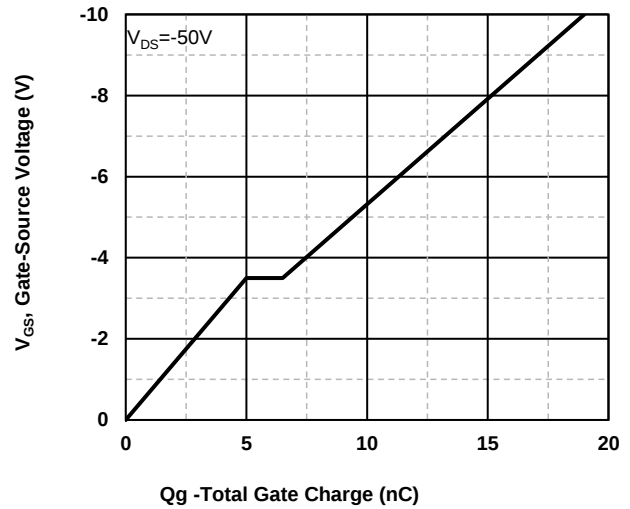


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

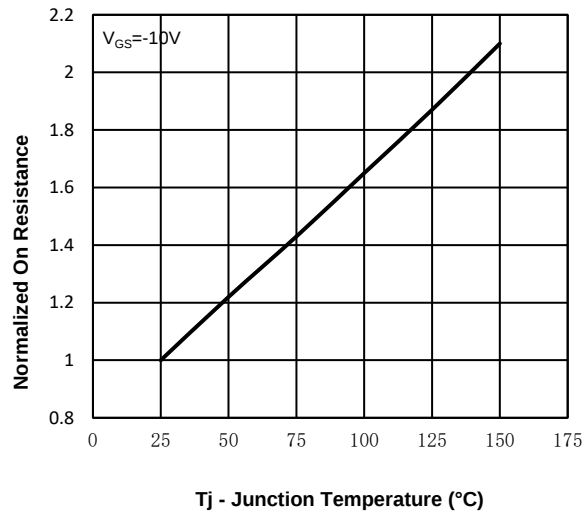


Fig3. Normalized On-Resistance Vs. Temperature

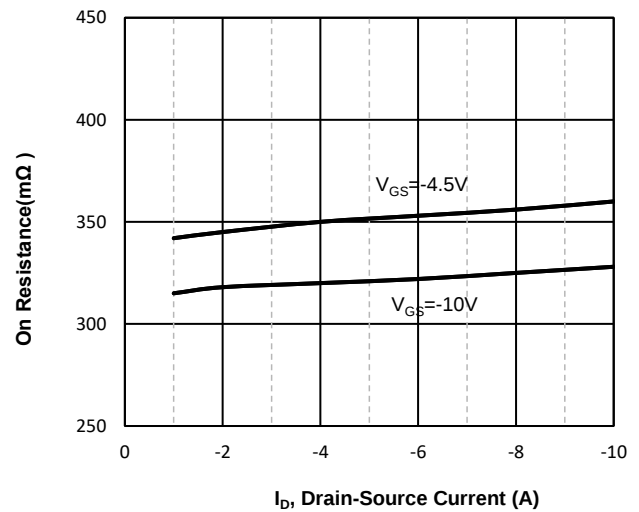


Fig4. On-Resistance Vs. Drain-Source Current

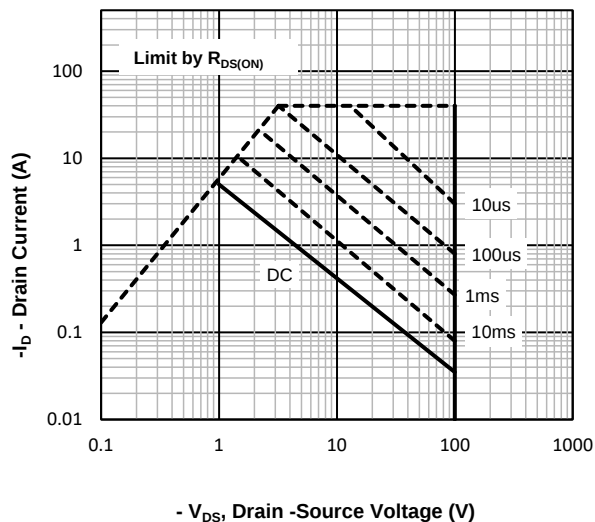


Fig5. Maximum Safe Operating Area

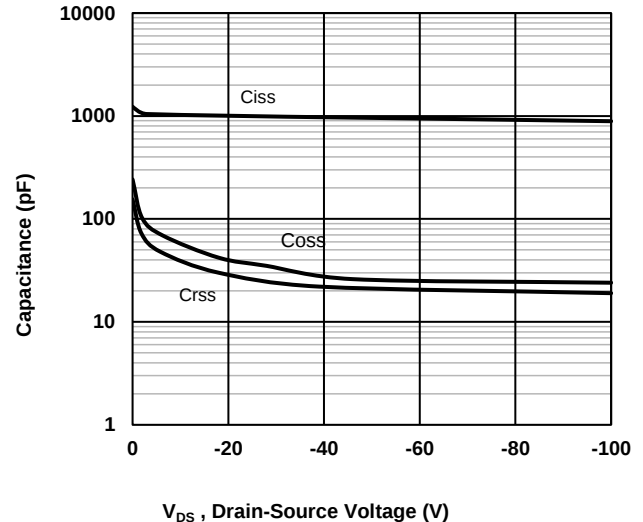
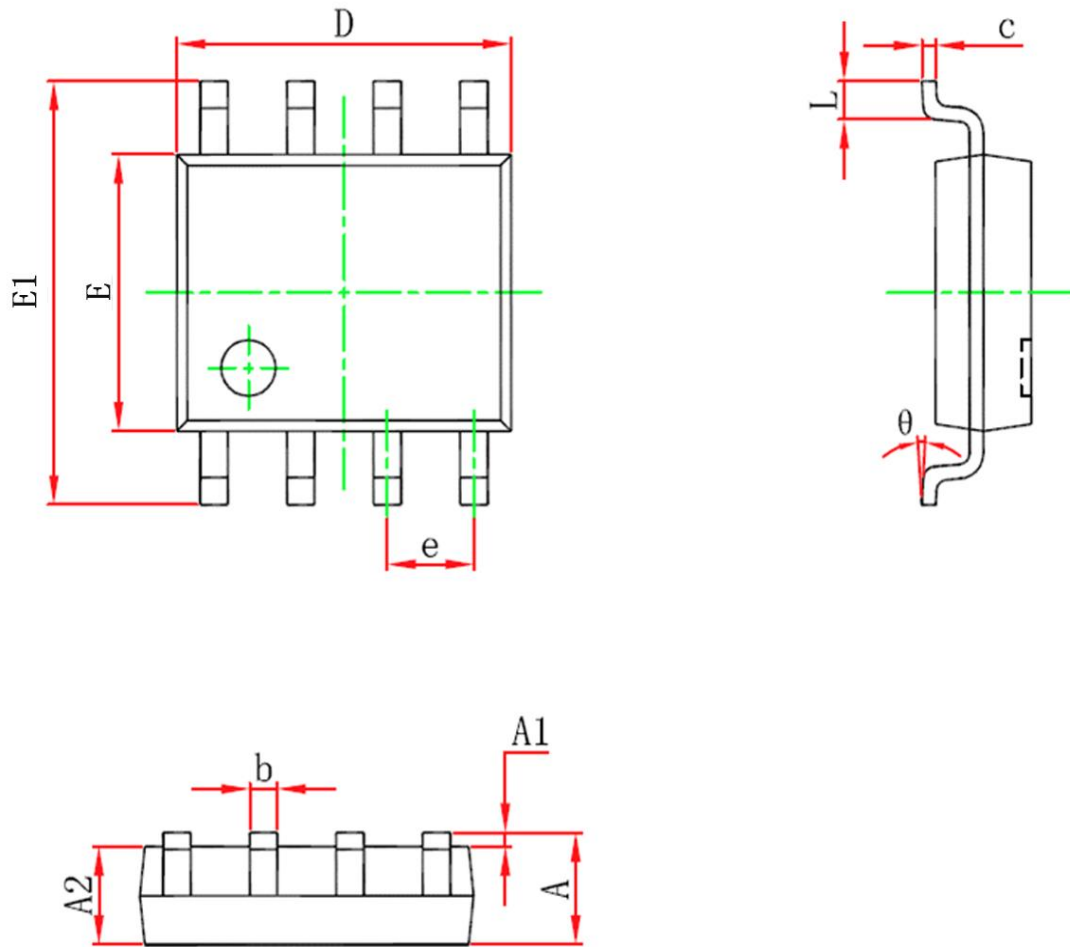


Fig6. Typical Capacitance Vs. Drain-Source Voltage

SOP-8 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	1.450	1.750	0.057	0.068
A1	0.100	0.250	0.003	0.009
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.012	0.020
c	0.170	0.250	0.006	0.009
D	4.700	5.100	0.185	0.200
e	1.270(BSC)		0.050(BSC)	
E	3.800	4.000	0.149	0.157
E1	5.800	6.200	0.228	0.244
L	0.400	1.270	0.015	0.050
θ	0°	8°	0°	8°